SLAS492-SEPTEMBER 2005



# 12-Bit, 1-MSPS, MICRO-POWER, MINIATURE SAR ANALOG-TO-DIGITAL CONVERTERS

#### **FEATURES**

- 1-MHz Sample Rate Serial Device
- 12-Bit Resolution
- Zero Latency
- 20-MHz Serial Interface
- Supply Range: 2.35 V to 5.25 V
- Typical Power Dissipation at 1 MSPS:
  - 3.9 mW at 3-V  $V_{DD}$
  - 7.5 mW at 5-V  $V_{DD}$
- INL ±1.25 LSB Maximum, ±0.65 LSB (Typical)
- DNL ±1 LSB Maximum, +0.4 / -0.65 LSB (Typical)
- Typical AC Performance:
   72.25 dB SINAD, -84 dB THD
- Unipolar Input Range: 0 V to V<sub>DD</sub>
- Power Down Current: 1 μA
- Wide Input Bandwidth: 15 MHz at 3 dB
- 6-Pin SOT23 and SC70 Packages

#### **APPLICATIONS**

- Base Band Converters in Radio Communication
- Motor Current/Bus Voltage Sensors in Digital Drives
- Optical Networking (DWDM, MEMS Based Switching)
- Optical Sensors
- Battery Powered Systems
- Medical Instrumentations
- High-Speed Data Acquisition Systems
- High-Speed Closed-Loop Systems

#### DESCRIPTION

The ADS7886 is a 12-bit, 1-MSPS analog-to-digital converter (ADC). The device includes a capacitor based SAR A/D converter with inherent sample and hold. The serial interface in each device is controlled by the  $\overline{CS}$  and SCLK signals for glueless connections with microprocessors and DSPs. The input signal is sampled with the falling edge of  $\overline{CS}$ , and SCLK is used for conversion and serial data output.

The device operates from a wide supply range from 2.35 V to 5.25 V. The low power consumption of the device makes it suitable for battery-powered applications. The device also includes a powerdown feature for power saving at lower conversion speeds.

The high level of the digital input to the device is not limited to device  $V_{DD}$ . This means the digital input can go as high as 5.25 V when device supply is 2.35 V. This feature is useful when digital signals are coming from other circuit with different supply levels. Also this relaxes restriction on power up sequencing.

The ADS7886 is available in 6-pin SOT23 and SC70 packages and is specified for operation from -40°C to 125°C.

#### Micro-Power Miniature SAR Converter Family

BIT	< 300 KSPS	300 KSPS – 1.25 MSPS
12-Bit	ADS7866 (1.2 V <sub>DD</sub> to 3.6 V <sub>DD</sub> )	ADS7886 (2.35 V <sub>DD</sub> to 5.25 V <sub>DD</sub> )
10-Bit	ADS7867 (1.2 V <sub>DD</sub> to 3.6 V <sub>DD</sub> )	ADS7887 (2.35 V <sub>DD</sub> to 5.25 V <sub>DD</sub> )
8-Bit	ADS7868 (1.2 V <sub>DD</sub> to 3.6 V <sub>DD</sub> )	ADS7888 (2.35 V <sub>DD</sub> to 5.25 V <sub>DD</sub> )

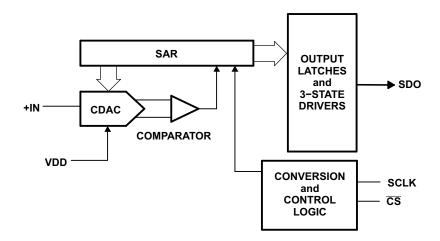


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.



## PACKAGE/ORDERING INFORMATION(1)

DEVICE	MAXIMUM INTEGRAL LINEARITY (LSB)	MAXIMUM DIFFER- ENTIAL LINEARITY (LSB)	NO MISSING CODES AT RESOLUTION (BIT)	PACK- AGE TYPE	PACK- AGE DESIG- NATOR	TEMPERATURE RANGE	PACKAGE MARKING	ORDERING INFORMATION	TRANSPORT MEDIA QUANTITY	
				6-Pin SOT23	DBV	DDV.		BBAQ	ADS7886SBDBVT	Tape and reel 250
ADS7886SB	±1.25	±1	12			−40°C to 125°C	BBAQ	ADS7886SBDBVR	Tape and reel 3000	
ADS/6005B	±1.23			6-Pin SC70	DCK		BNL	ADS7886SBDCKT	Tape and reel 250	
								ADS7886SBDCKR	Tape and reel 3000	
				6-Pin	DBV		BBAQ	ADS7886SDBVT	Tape and reel 250	
AD070000			44	SOT23				ADS7886SDBVR	Tape and reel 3000	
ADS7886S	±2	±2	11	6-Pin		-40°C to 125°C		ADS7886SDCKT	Tape and reel 250	
				SC70	DCK		BNL	ADS7886SDCKR	Tape and reel 3000	

<sup>(1)</sup> For most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



# ABSOLUTE MAXIMUM RATINGS(1)

		UNIT
+IN to AGND	-0.3 V to +V <sub>DD</sub> +0.3 V	
+V <sub>DD</sub> to AGND		−0.3 V to 7 V
Digital input voltage to GND		-0.3 V to (7 V)
Digital output to GND		-0.3 V to (+V <sub>DD</sub> + 0.3 V)
Operating temperature range	−40°C to 125°C	
Storage temperature range	−65°C to 150°C	
Junction temperature (T <sub>J</sub> Max)		150°C
Power dissipation, SOT23 and S	C70 packages	$(T_J Max-T_A)/\theta_{JA}$
0 Thermal impedance	SOT23	295.2°C/W
θ <sub>JA</sub> Thermal impedance	SC70	351.3°C/W
Lood tomporature coldering	Vapor phase (60 sec)	215°C
Lead temperature, soldering	Infrared (15 sec)	220°C

<sup>(1)</sup> Stresses above those listed under absolute maximum ratings may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS**

+V<sub>DD</sub> = 2.35 V to 5.25 V,  $T_A = -40^{\circ}C$  to 125°C,  $f_{(sample)} = 1$  MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
ANAL	OG INPUT				,		
	Full-scale input voltage span <sup>(1)</sup>		0		$V_{DD}$	V	
	Absolute input voltage range	+IN	-0.2		V <sub>DD</sub> +0.2	V	
C <sub>I</sub>	Input capacitance (2)			21		pF	
I <sub>lkg</sub>	Input leakage current	T <sub>A</sub> = 125°C		40		nA	
SYSTE	M PERFORMANCE		l		,		
	Resolution			12		Bits	
	No estado a contra	ADS7886SB	12			D:1-	
	No missing codes	ADS7886S	11			Bits	
INII	Lateranal annulla conflic	ADS7886SB	-1.25	±0.65	1.25	. 05 (2)	
INL	Integral nonlinearity	ADS7886S	2		2	LSB <sup>(3)</sup>	
-	Differential coefficients	ADS7886SB	-1	+0.4/-0.65	1	LSB	
DNL	Differential nonlinearity	ADS7886S	-2		2	LOD	
ı	O(1 ) (A)	V <sub>DD</sub> = 2.35 V to 3.6 V	-2.5	±0.5	2.5	1.00	
E <sub>O</sub>	Offset error <sup>(4)</sup>	V <sub>DD</sub> = 4.75 V to 5.25 V	-2	±0.5	2	LSB	
E <sub>G</sub>	Gain error		-1.75	±0.5	1.75	LSB	
SAMP	LING DYNAMICS		l		,		
	Conversion time	20-MHz SCLK	760	800		ns	
	Acquisition time		325			ns	
	Maximum throughput rate	20-MHz SCLK			1	MHz	
	Aperture delay			5		ns	
	Step Response			160		ns	
	Overvoltage recovery			160		ns	
DYNA	WIC CHARACTERISTICS	-	ı				
ONID	O'mand to analyze matic	$V_{DD} = 2.35 \text{ V to } 3.6 \text{ V}, f_{I} = 100 \text{ kHz}$	69	71.25		-ID	
SNR	Signal-to-noise ratio	$V_{DD} = 4.75 \text{ V to } 5.25 \text{ V, } f_{I} = 100 \text{ kHz}$	70	72.25		dB	

- (1) Ideal input span; does not include gain or offset error.(2) See Figure 28 for details on the sampling circuit.
- LSB means least significant bit.
- Measured relative to an ideal full-scale input.



# **ELECTRICAL CHARACTERISTICS (continued)**

+V<sub>DD</sub> = 2.35 V to 5.25 V,  $T_A = -40^{\circ}C$  to 125°C,  $f_{(sample)} = 1$  MHz (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
CINIAD	Cinnel to union and distantion	$V_{DD} = 2.35 \text{ V to } 3.6 \text{ V}, f_{I} = 100 \text{ kHz}$	69	71.25		٦D	
SINAD	Signal-to-noise and distortion	V <sub>DD</sub> = 4.75 V to 5.25 V, f <sub>I</sub> = 100 kHz	70	72.25		dB	
THD	Total harmonic distortion <sup>(5)</sup>	f <sub>I</sub> = 100 kHz		-84		dB	
SFDR	Spurious free dynamic range	f <sub>I</sub> = 100 kHz		85.5		dB	
	Full power bandwidth	At –3 dB		15		MHz	
DIGITA	L INPUT/OUTPUT				·		
Logic fa	mily — CMOS						
V <sub>IH</sub>	High-level input voltage	V <sub>DD</sub> = 2.35 V to 5.25 V	V <sub>DD</sub> - 0.4		5.25	V	
	Lavalaval innut valta aa	V <sub>DD</sub> = 5 V			0.8		
$V_{IL}$	Low-level input voltage	V <sub>DD</sub> = 3 V			0.4	V	
V <sub>OH</sub>	High-level output voltage	I <sub>(source)</sub> = 200 μA	V <sub>DD</sub> -0.2			V	
V <sub>OL</sub>	Low-level output voltage	I <sub>(sink)</sub> = 200 μA			0.4	V	
POWER	SUPPLY REQUIREMENTS				·		
+V <sub>DD</sub>	Supply voltage		2.35	3.3	5.25	V	
		$V_{DD}$ = 2.35 V to 3.6 V, 1-MHz throughput		1.3	1.5		
	Supply current (normal mode)	V <sub>DD</sub> = 4.75 V to 5.25 V, 1-MHz throughput		1.5	2	mA	
		V <sub>DD</sub> = 2.35 V to 3.6 V, static state	3.6 V, static state		1.1		
		V <sub>DD</sub> = 4.75 V to 5.25 V, static state			1.5		
	Device device state events events	SCLK off			1		
	Power down state supply current	SCLK on (20 MHz)			200	μΑ	
	Dower discinstion at 1 MHz throughout	V <sub>DD</sub> = 3 V	3.9		4.5	mW	
	Power dissipation at 1-MHz throughput	V <sub>DD</sub> = 5 V		7.5 10			
	Dower dissinction is state	V <sub>DD</sub> = 3 V			3.3	m1/1/	
	Power dissipation in static state	V <sub>DD</sub> = 5 V	7.5		7.5	mW	
	Power up time				0.1	μs	
	Invalid conversions after power up or reset				1		

<sup>(5)</sup> Calculated on the first nine harmonics of the input frequency.



# TIMING REQUIREMENTS (see Figure 1 and Figure 2)

All specifications typical at  $T_A = -40^{\circ}\text{C}$  to 125°C,  $V_{DD} = 2.35 \text{ V}$  to 5.25 V (unless otherwise specified).

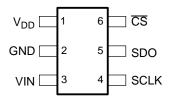
	PARAMETER		TEST CONDITIONS <sup>(1)</sup>	MIN	TYP	MAX	UNIT				
	Communication times	AD07000	V <sub>DD</sub> = 3 V			16 × t <sub>SCLK</sub>	ns				
t <sub>conv</sub>	Conversion time	ADS7866	V <sub>DD</sub> = 5 V			16 × t <sub>SCLK</sub>					
	Minimum quiet time needed from bu	s 3-state to start	V <sub>DD</sub> = 3 V	40							
t <sub>q</sub>	of next conversion		V <sub>DD</sub> = 5 V	40			ns				
	Deleviting OC law to first data (0) a		V <sub>DD</sub> = 3 V		15	25	ns				
t <sub>d1</sub>	Delay time, $\overline{CS}$ low to first data (0) of	out	V <sub>DD</sub> = 5 V		13	25	ns				
	Catura tima OC laur ta COLIV laur		V <sub>DD</sub> = 3 V	10							
t <sub>su1</sub>	Setup time, CS low to SCLK low	Setup time, CS low to SCLK low					ns				
	Delevides and Collins to CDC		V <sub>DD</sub> = 3 V		15	25	ns				
t <sub>d2</sub>	Delay time, SCLK falling to SDO		V <sub>DD</sub> = 5 V		13	25					
	Held Co. a. OOLK felling to date on lid	1(2)	V <sub>DD</sub> < 3 V	7							
t <sub>h1</sub>	Hold time, SCLK falling to data valid	(2)	V <sub>DD</sub> > 5 V	5.5			ns				
	Delay time, 16th SCLK falling edge to SDO 3-state		V <sub>DD</sub> = 3 V		10	25	ns				
t <sub>d3</sub>			V <sub>DD</sub> = 5 V		8	20					
	D		V <sub>DD</sub> = 3 V	25	40						
t <sub>w1</sub>	Pulse duration, CS		V <sub>DD</sub> = 5 V	25	40		ns				
	Delevities AC bish to ODO 0 state		V <sub>DD</sub> = 3 V		17	30	ns				
t <sub>d4</sub>	Delay time, $\overline{\text{CS}}$ high to SDO 3-state		V <sub>DD</sub> = 5 V		15	25					
	Dulas duration COLK binb		V <sub>DD</sub> = 3 V	$0.4 \times t_{SCLK}$							
t <sub>wH</sub>	Pulse duration, SCLK high		V <sub>DD</sub> = 5 V	$0.4 \times t_{SCLK}$			ns				
	Dula duratia a COLK laur		V <sub>DD</sub> = 3 V	$0.4 \times t_{SCLK}$							
$t_{wL}$	Pulse duration, SCLK low		V <sub>DD</sub> = 5 V	$0.4 \times t_{SCLK}$			ns				
	F	CLK				20	T				
	Frequency, SCLK					20	MHz				
		econd falling edge of clock and CS to		-2		5					
t <sub>d5</sub>	enter in powerdown (use min spec r enter in powerdown) Figure 2	not to accidently	V <sub>DD</sub> = 5 V	-2		5	ns				
_	Delay time, CS and 10th falling edge		V <sub>DD</sub> = 3 V	2		-5					
t <sub>d6</sub>	enter in powerdown (use max spec enter in powerdown) Figure 2	not to accidently	V <sub>DD</sub> = 5 V	2		-5	ns				

<sup>(1) 3-</sup>V Specifications apply from 2.35 V to 3.6 V, and 5-V specifications apply from 4.75 V to 5.25 V.(2) With 50-pf load.



#### **DEVICE INFORMATION**

#### SOT23/SC70 PACKAGE (TOP VIEW)



#### **TERMINAL FUNCTIONS**

TER	TERMINAL		DESCRIPTION					
NAME	NO.	I/O	DESCRIPTION					
$V_{DD}$	1	_	Power supply input also acts like a reference voltage to ADC.					
GND	2	_	Ground for power supply, all analog and digital signals are referred with respect to this pin.					
VIN	3	I	Analog signal input					
SCLK	4	I	Serial clock					
SDO	5	0	Serial data out					
CS	6	I	Chip select signal, active low					

#### **NORMAL OPERATION**

The cycle begins with the falling edge of  $\overline{CS}$ . This point is indicated as **a** in Figure 1. With the falling edge of  $\overline{CS}$ , the input signal is sampled and the conversion process is initiated. The device outputs data while the conversion is in progress. The data word contains 4 leading zeros, followed by 12-bit data in MSB first format.

The falling edge of  $\overline{CS}$  clocks out the first zero, and a zero is clocked out on every falling edge of the clock until the third edge. Data is in MSB first format with the MSB being clocked out on the 4th falling edge. On the 16th falling edge of SCLK, SDO goes to the 3-state condition. The conversion ends on the 16th falling edge of SCLK. The device enters the acquisition phase on the first rising edge of SCLK after the 13th falling edge. This point is indicated by **b** in Figure 1.

 $\overline{\text{CS}}$  can be asserted (pulled high) after 16 clocks have elapsed. It is necessary not to start the next conversion by pulling  $\overline{\text{CS}}$  low until the end of the quiet time (t<sub>q</sub>) after SDO goes to 3-state. To continue normal operation, it is necessary that  $\overline{\text{CS}}$  is not pulled high until point **b**. Without this, the device does not enter the acquisition phase and no valid data is available in the next cycle. (Also refer to power down mode for more details.)  $\overline{\text{CS}}$  going high any time after the conversion start aborts the ongoing conversion and SDO goes to 3-state.

The high level of the digital input to the device is not limited to device  $V_{DD}$ . This means the digital input can go as high as 5.25 V when the device supply is 2.35 V. This feature is useful when digital signals are coming from another circuit with different supply levels. Also, this relaxes the restriction on power up sequencing. However, the digital output levels ( $V_{OH}$  and  $V_{OL}$ ) are governed by  $V_{DD}$  as listed in the *Electrical Characteristics* table.

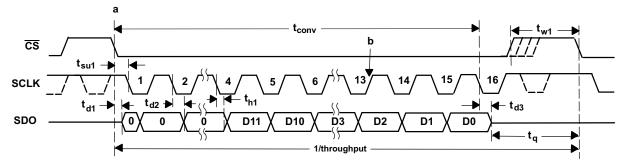


Figure 1. Interface Timing Diagram



#### **POWER DOWN MODE**

The device enters power down mode if  $\overline{\text{CS}}$  goes high anytime after the 2nd SCLK falling edge to before the 10th SCLK falling edge. Ongoing conversion stops and SDO goes to 3-state under this power down condition as shown in Figure 2.

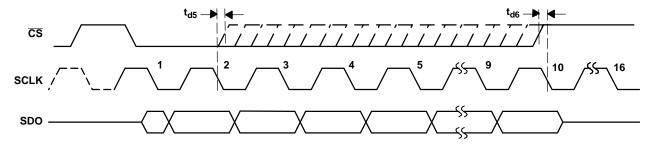


Figure 2. Entering Power Down Mode

A dummy cycle with  $\overline{CS}$  low for more than 10 SCLK falling edges brings the device out of power down mode. For the device to come to the fully powered up condition it takes 1  $\mu s$ .  $\overline{CS}$  can be pulled high any time after the 10th falling edge as shown in Figure 3. It is not necessary to continue until the 16th clock if the next conversion starts 1  $\mu s$  after  $\overline{CS}$  going low of the dummy cycle and the quiet time ( $t_q$ ) condition is met.

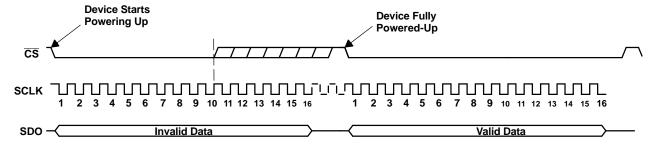
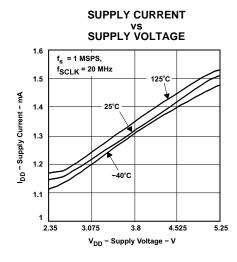
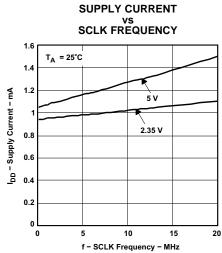


Figure 3. Exiting Power Down Mode



#### **TYPICAL CHARACTERISTICS**





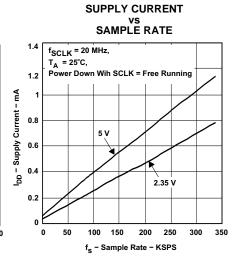


Figure 4.

Figure 5.

Figure 6.



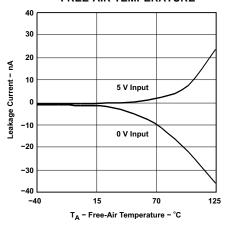
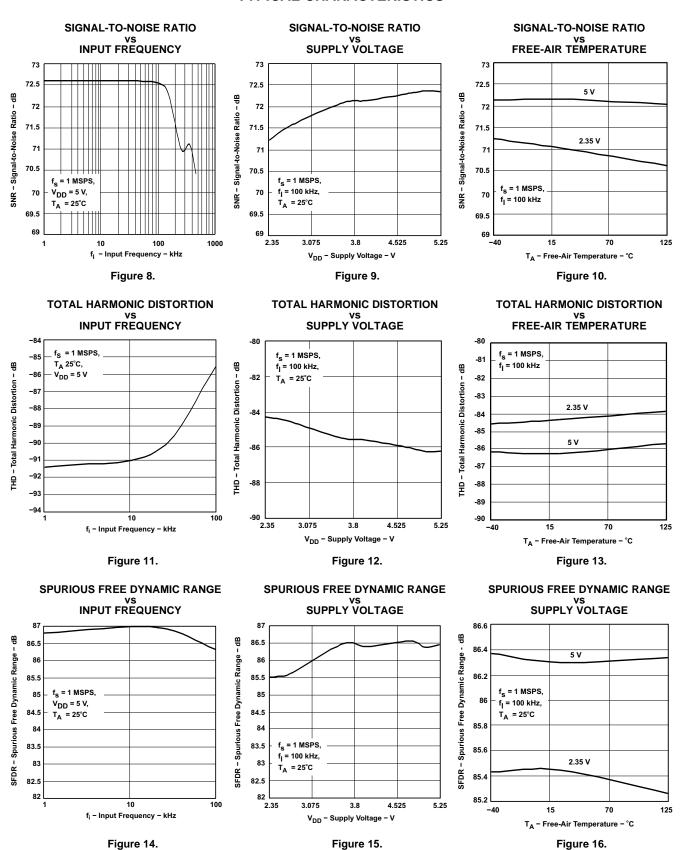


Figure 7.

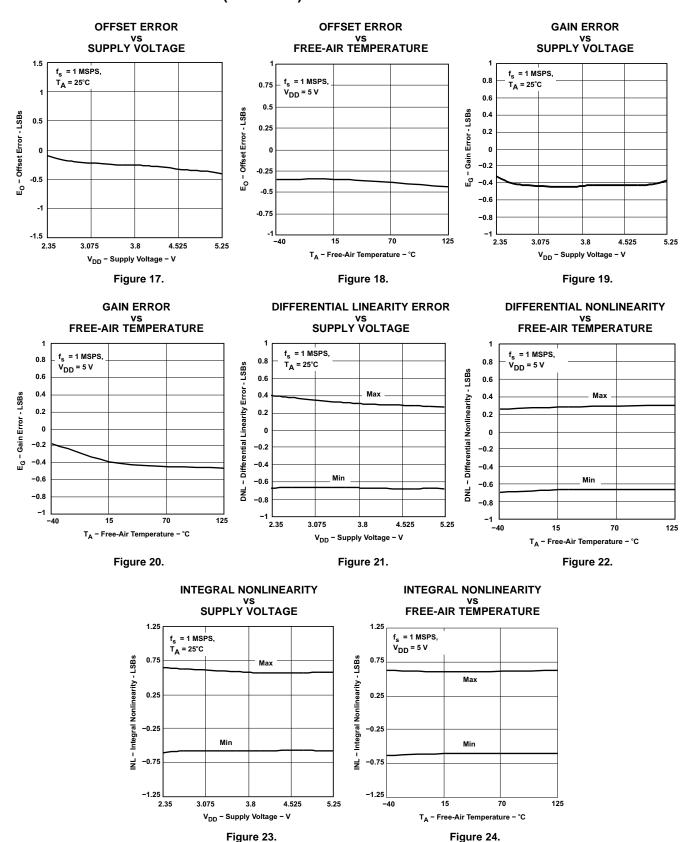


#### **TYPICAL CHARACTERISTICS**



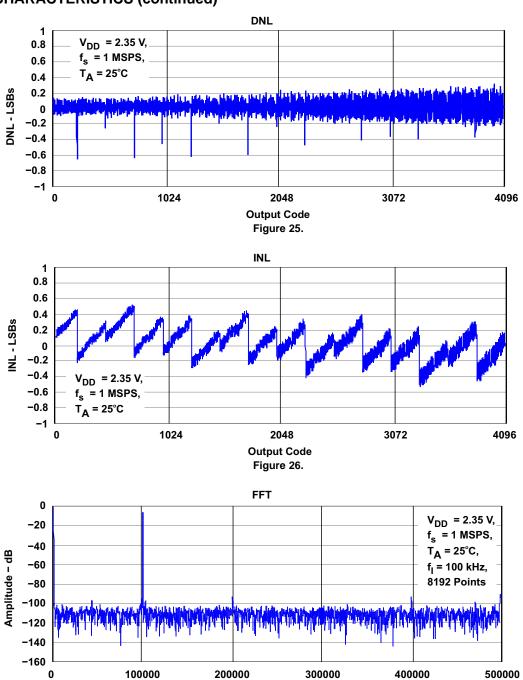


# **TYPICAL CHARACTERISTICS (continued)**





### **TYPICAL CHARACTERISTICS (continued)**



f - Frequency - Hz Figure 27.



#### APPLICATION INFORMATION

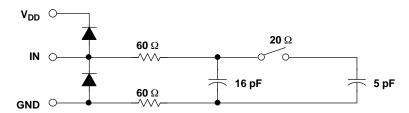


Figure 28. Typical Equivalent Sampling Circuit

#### Driving the VIN and V<sub>DD</sub> Pins

The VIN input should be driven with a low impedance source. In most cases additional buffers are not required. In cases where the source impedance exceeds 200  $\Omega$ , using a buffer would help achieve the rated performance of the converter. The THS4031 is a good choice for the driver amplifier buffer.

The reference voltage for the A/D converter is derived from the supply voltage internally. The devices offer limited low-pass filtering functionality on-chip. The supply to these converters should be driven with a low impedance source and should be decoupled to the ground. A 1-µF storage capacitor and a 10-nF decoupling capacitor should be placed close to the device. Wide, low impedance traces should be used to connect the capacitor to the pins of the device. The ADS7886 draws very little current from the supply lines. The supply line can be driven by either:

- Directly from the system supply.
- A reference output from a low drift and low drop out reference voltage generator like REF3030 or REF3130.
   The ADS7886 operates from a wide range of supply voltages. The actual choice of the reference voltage generator would depend upon the system. Figure 30 shows one possible application circuit.
- A low-pass filtered system supply followed by a buffer, like the zero-drift OPA735, can also be used in cases
  where the system power supply is noisy. Care should be taken to ensure that the voltage at the V<sub>DD</sub> input
  does not exceed 7 V to avoid damage to the converter. This can be done easily using single supply CMOS
  amplifiers like the OPA735. Figure 31 shows one possible application circuit.

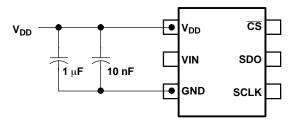


Figure 29. Supply/Reference Decoupling Capacitors

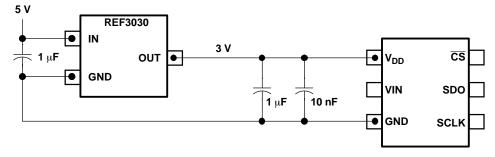


Figure 30. Using the REF3030 Reference



# **APPLICATION INFORMATION (continued)**

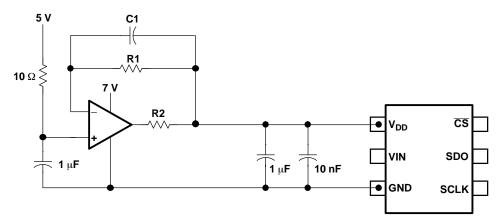


Figure 31. Buffering with the OPA735





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#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
ADS7886SBDBVR	ACTIVE	SOT-23	DBV	6	3000	TBD	CU SN	Level-2-260C-1 YEAR
ADS7886SBDBVT	ACTIVE	SOT-23	DBV	6	250	TBD	CU SN	Level-2-260C-1 YEAR
ADS7886SBDCKR	ACTIVE	SC70	DCK	6	3000	TBD	CU SN	Level-2-260C-1 YEAR
ADS7886SBDCKT	ACTIVE	SC70	DCK	6	250	TBD	CU SN	Level-2-260C-1 YEAR
ADS7886SDBVR	ACTIVE	SOT-23	DBV	6	3000	TBD	Call TI	Call TI
ADS7886SDBVT	ACTIVE	SOT-23	DBV	6	250	TBD	CU SN	Level-2-260C-1 YEAR
ADS7886SDCKR	ACTIVE	SC70	DCK	6	3000	TBD	Call TI	Call TI
ADS7886SDCKT	ACTIVE	SC70	DCK	6	250	TBD	CU SN	Level-2-260C-1 YEAR

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

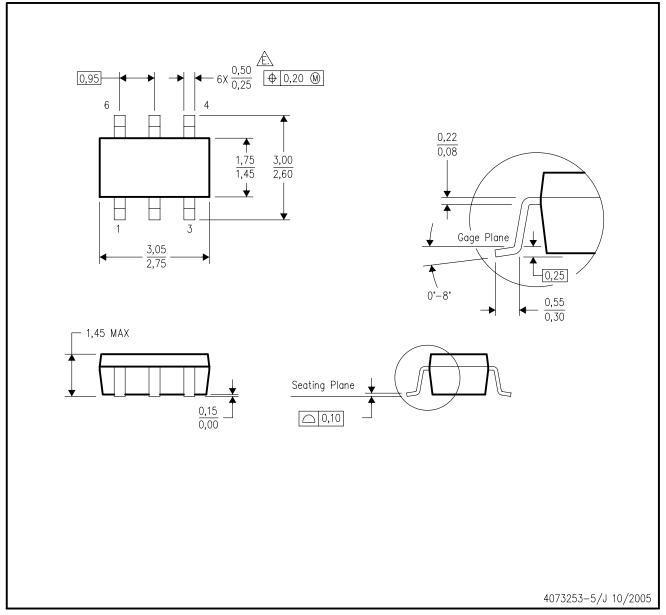
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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# DBV (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



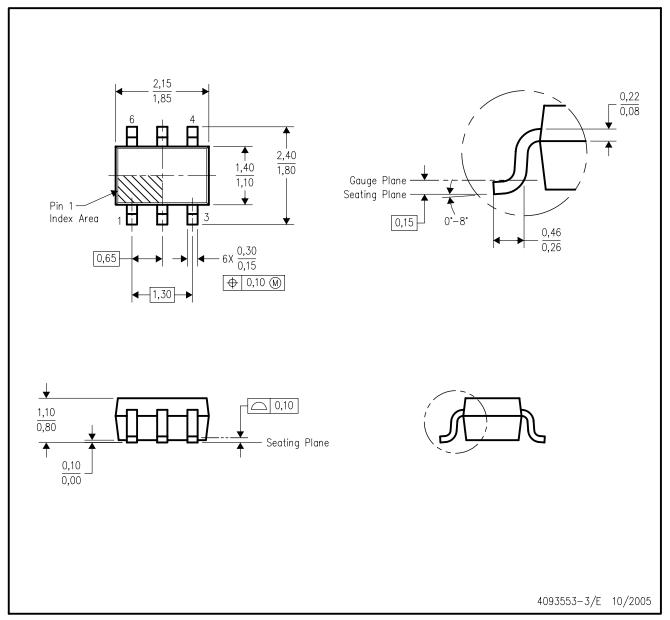
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



# DCK (R-PDSO-G6)

# PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AB.



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